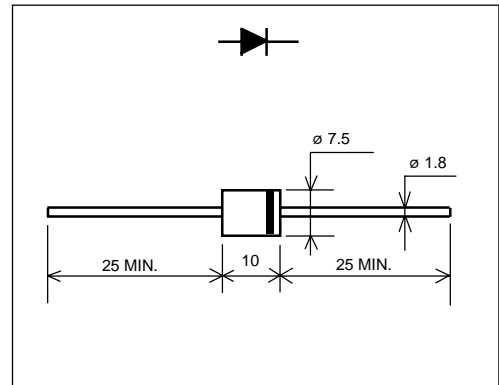


FAST RECOVERY DIODE

■ Outline drawings, mm



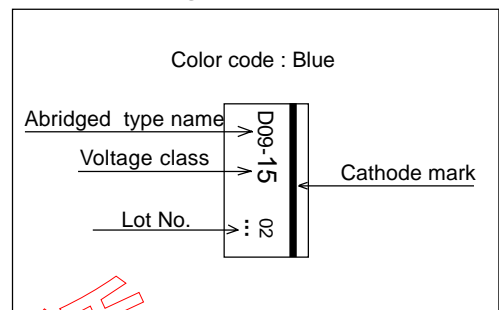
■ Features

- Large current
- High voltage by mesa design
- High reliability

■ Applications

- High speed switching

■ Marking



■ Maximum ratings and characteristics

- Absolute maximum ratings

Item	Symbol	Conditions	Rating		Unit
			-13	-15	
Repetitive peak reverse voltage	V_{RRM}		1300	1500	V
Average forward current	$I_{F(AV)}$	Resistive load ($T_I=100^{\circ}\text{C}$)	3.0		A
Surge current	I_{FSM}	Sine wave 10ms	50		A
Operating junction temperature	T_j		-40 to +150		$^{\circ}\text{C}$
Storage temperature	T_{stg}		-40 to +150		$^{\circ}\text{C}$

- Electrical characteristics ($T_a=25^{\circ}\text{C}$ Unless otherwise specified)

Item	Symbol	Conditions	Max.	Unit
Forward voltage drop	V_{FM}	$I_{FM}=4.0\text{A}$	1.5	V
Reverse current	I_{RRM}	$V_R=V_{RRM}$	50	μA
Reverse recovery time	t_{rr}	$I_F=0.1\text{A}$, $I_R=0.1\text{A}$	0.6	μs

■ Characteristics

